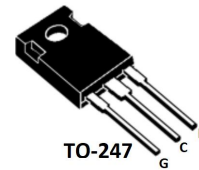


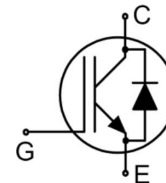
Features

- Low gate charge
- Trench FS Technology
- RoHS product



Applications

- General purpose inverters
- Induction heating(IH)
- UPS



Absolute Ratings (T_c=25°C)

Parameter	Symbol	Value	Unit
Collector-Emmitter Voltage	V _{CES}	1200	V
*Collector Current-continuous	I _c T=25°C T=100°C	30	A
		15	A
Collector Current-pulse(note 1)	I _{CM}	45	A
Diode Continuous forward current	I _F T=25°C T=100°C	30	A
		15	
Diode Maximum Forward Current (Note 1)	I _{FM}	45	A
Gate-Emmitter Voltage	V _{GES}	±20	V
Power Dissipation(TO-247)	P _D T _C =25°C	238	W
Operating Temperature Range	T _J	-40~+175	°C
Storage Temperature Range	T _{STG}	-55~+150	°C
Maximum Lead Temperature for Soldering Purposes	T _L	300	°C

*Collector current limited by maximum Junction temperature

Electrical Characteristic(T_C=25°C unless otherwise noted)

Parameter	Symbol	Tests conditions	Min	Typ	Max	Units
Off-Characteristics						
Collector-Emmitter Voltage	BV _{CES}	I _C =250μA, V _{GE} =0V	1200	-	-	V
Zero Gate Voltage Collector Current	I _{CES}	V _{CE} =1200V, V _{GE} =0V, T _C =25°C	-	-	100	uA
		T _C =100°C	-	-	2	mA

Gate-body leakage current,reverse	I_{GESR}	$V_{CE}=0V, V_{GE}=\pm 20V$	-	-	± 150	nA
On-Characteristics						
Gate-Emmitter Threshold Voltage	$V_{GE(th)}$	$V_{CE}=V_{GE}, I_c=250\mu A$	4.5	-	6.5	V
Collector-Emmitter saturation Voltage	V_{CESAT}	$V_{GE}=15V, I_c=15A, T_c=25^\circ C$	-	1.6	2.1	V
		$T_c=125^\circ C$	-	1.9	-	V
		$T_c=150^\circ C$	-	2.1	-	V
Dynamic Characteristics						
Input capacitance	C_{ies}	$V_{CE}=25V, V_{GE}=0V, f=1.0MHz,$	-	1260	-	pF
Output capacitance	C_{oes}		-	78	-	pF
Reverse transfer capacitance	C_{res}		-	41	-	pF
Total Gate Charge	Q_g	$V_{CC}=960V, I_c=15A, V_{GE}=15V^{3,4}$	-	112	-	nC
Gate to emitter charge	Q_{ge}		-	8.8	-	
Gate to collector charge	Q_{gc}		-	80.7	-	
Switching Characteristics						
Turn-On delay time	$t_d(on)$	$V_{CE}=600V, I_c=15A, R_G=10\Omega, Inductive load T_c=25^\circ C$	-	10	-	ns
Turn-On rise time	t_r		-	34	-	ns
Turn-off delay time	$t_d(off)$		-	52	-	ns
Turn-off Fall time	t_f		-	174	-	ns
Turn-on energy	E_{on}		-	0.38	-	mJ
Turn-off energy	E_{off}		-	0.67	-	mJ
Total switching Energy	E_{tot}		-	1.05	-	mJ
Anti-Paraller Diode Characteristics and Maximum Ratings						
Diode Forward Voltage	V_F	$V_{GE}=0V, I_F=15A.$	-	1.85	2.2	V
Diode Reverse recovery time	t_{rr}	$V_{GE}=0V, V_R=600V, I_F=15A, di/dt=450A/us^4$	-	283	-	ns
Reverse recovery charge	Q_{rr}		-	1180	-	nC

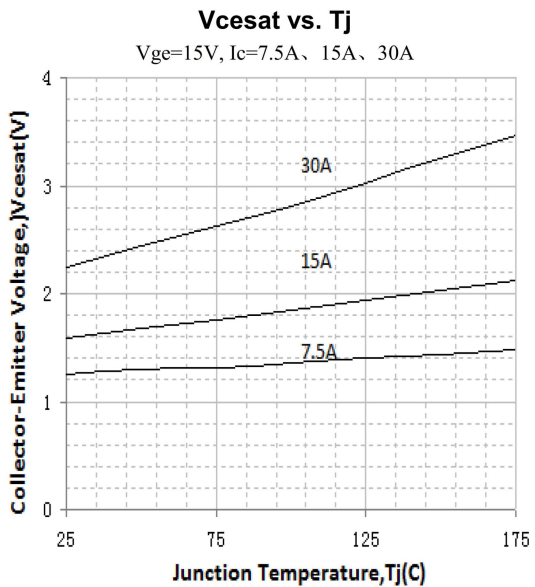
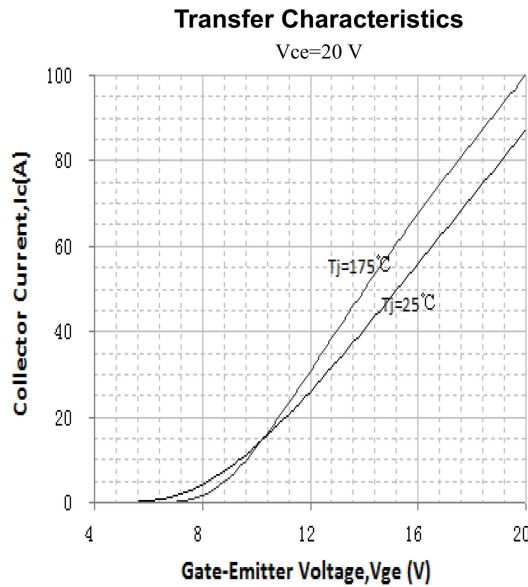
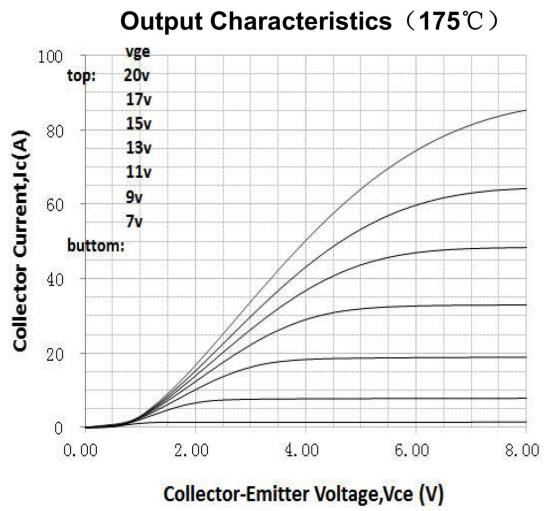
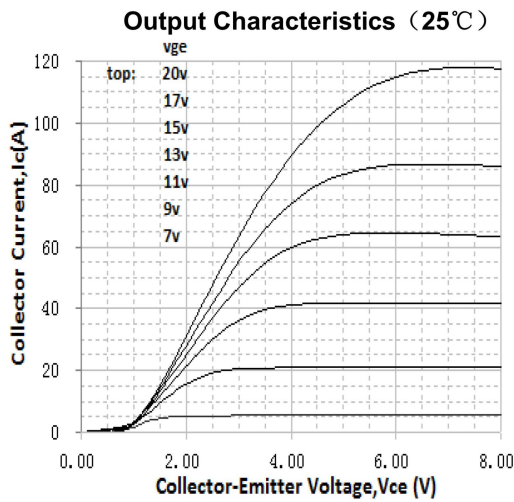
Thermal Characteristics

Symbol	Parameter	Type	Units
$R_{th j-c}$	Thermal Resistance, Junction to case	0.63	$^\circ C/W$
$R_{th j-a}$	Thermal Resistance, Junction to Ambient	40	$^\circ C/W$

Notes:

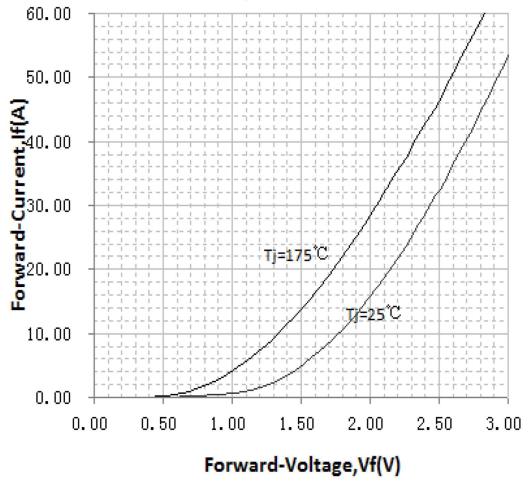
- 1: Pulse width limited by maximum junction temperature
- 2: Allowed number of short circuits: <1000; time between short circuits: >1s.
- 3: Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$
- 4: Essentially independent of operating temperature

Electrical Characteristics (curves)



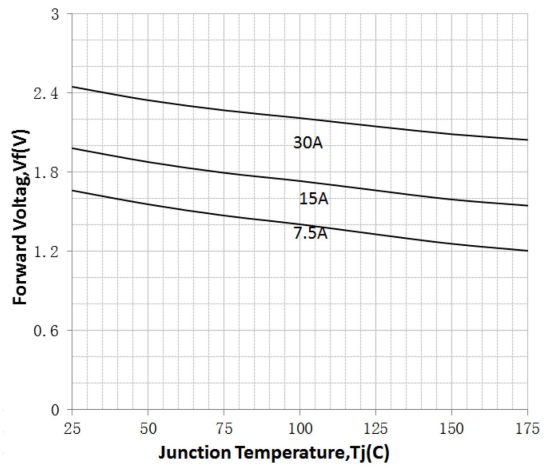
Diode Characteristic

$T_j=25^\circ\text{C}, 175^\circ\text{C}$



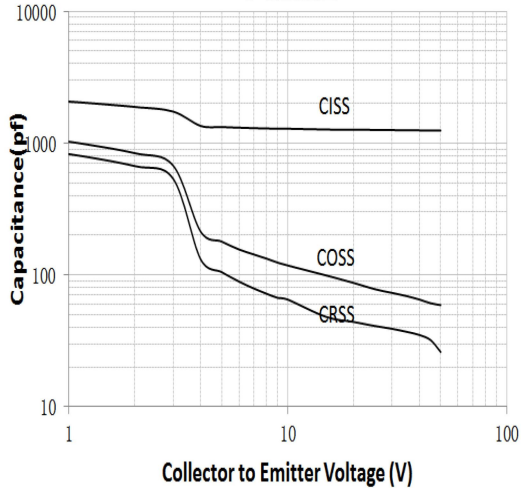
V_f vs. T_j

$I_c=7.5\text{A}, 15\text{A}, 30\text{A}$



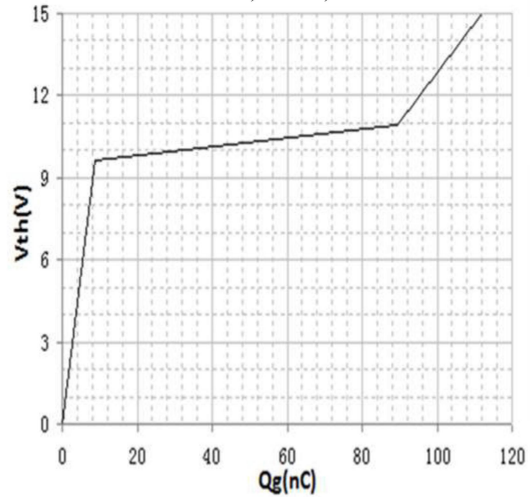
Capacitance Characteristic

$f=1.0\text{MHz}$



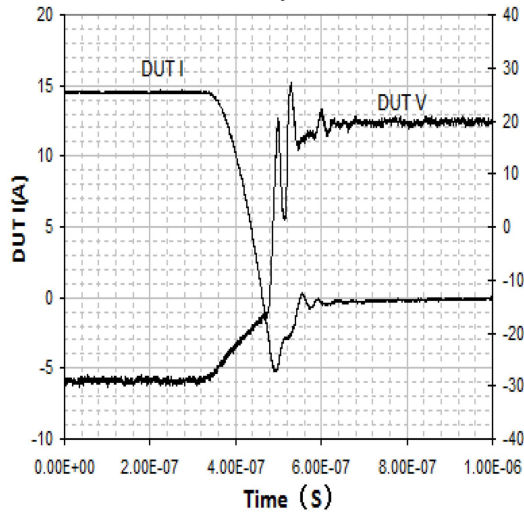
Gate Charge Characteristics

$V_{GE}=15\text{V}, I_c=15\text{A}, V_{CE}=960\text{V}$



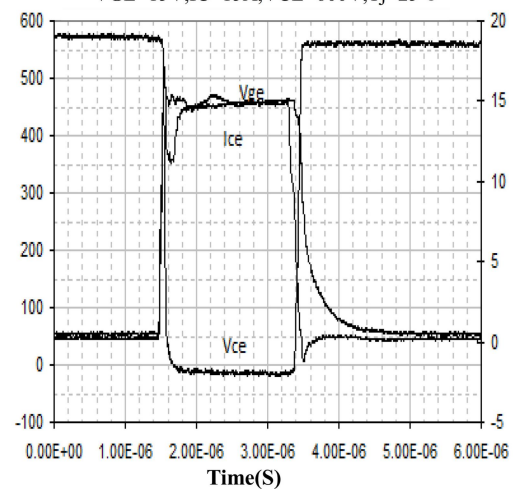
Diode Peak Reverse Recovery Current

$I_F=15\text{A}, T_j=25^\circ\text{C}$



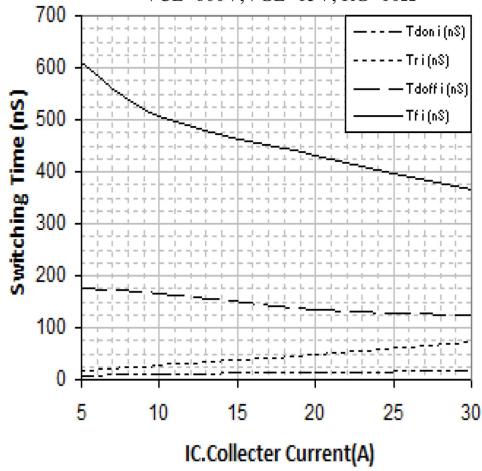
IGBT Switch

$V_{GE}=15\text{V}, I_c=15\text{A}, V_{CE}=600\text{V}, T_j=25^\circ\text{C}$



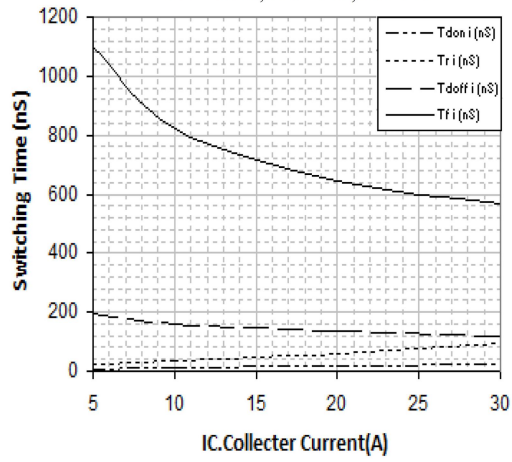
Switching Time vs. IC(25°C)

VCE=600V, VGE=15V, RG=10Ω



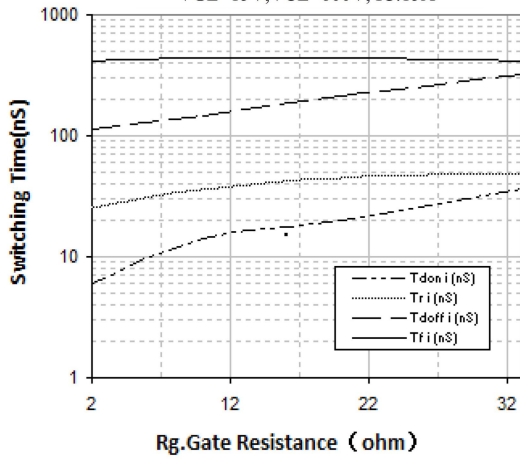
Switching Time vs. IC(175°C)

VCE=600V, VGE=15V, RG=10Ω



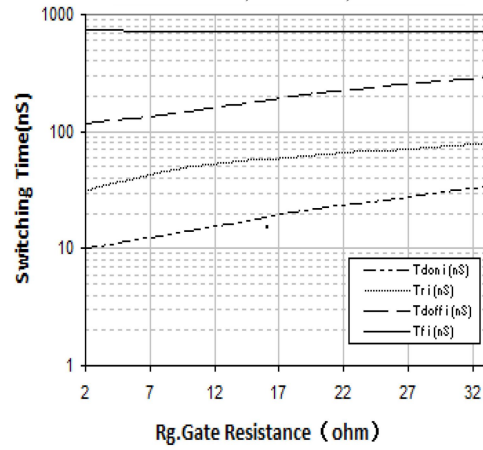
Switching Time vs. Rg(25°C)

VGE=15V, VCE=600V, IC=15A



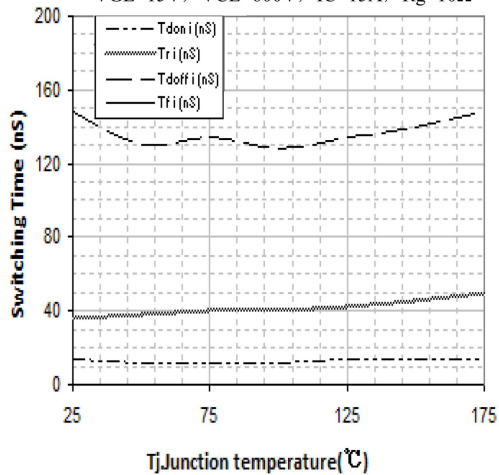
Switching Time vs. Rg(175°C)

VGE=15V, VCE=600V, IC=15A



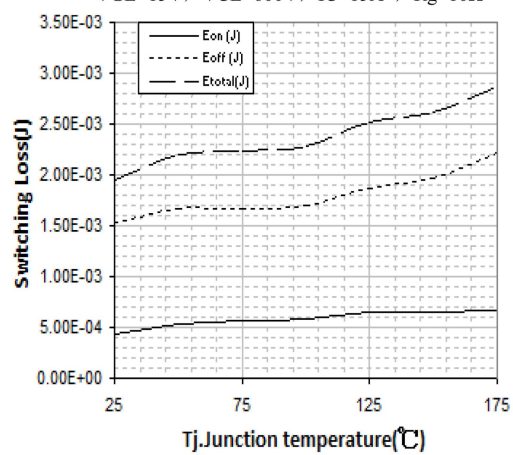
Switching Time vs. Tj

VGE=15V, VCE=600V, IC=15A, Rg=10Ω



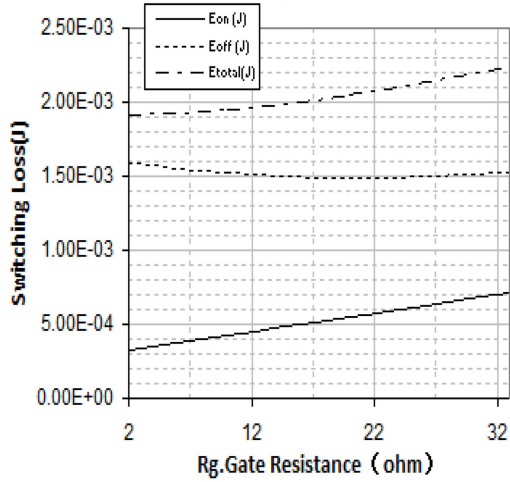
Switching Loss vs. Tj

VGE=15V, VCE=600V, IC=15A, Rg=10Ω



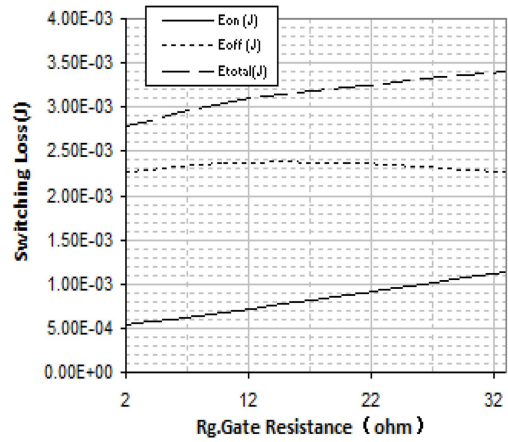
Switching Loss vs. Rg(25°C)

VGE=15V, VCE=600V, IC:15A



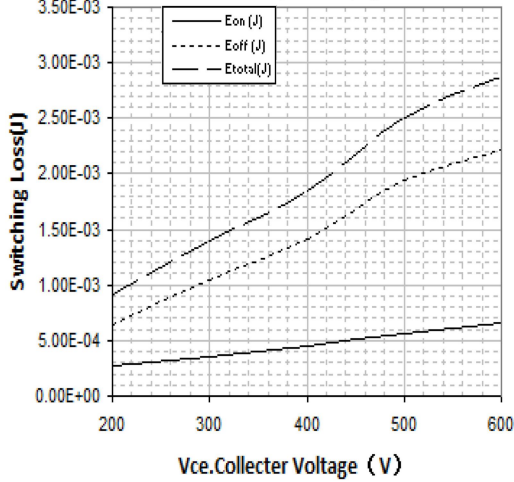
Switching Loss vs. Rg(175°C)

VGE=15V, VCE=600V, IC:15A



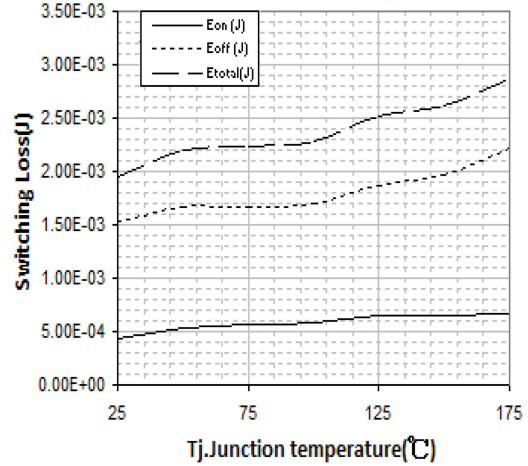
Switching Loss vs. VCE(175°C)

VGE=15V, IC:15A, Rg=10Ω



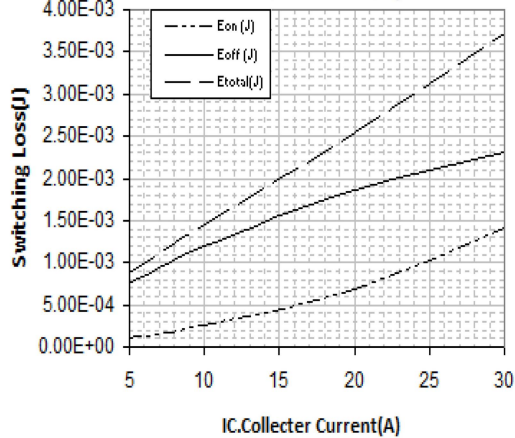
Switching Loss vs. Tj

VGE=15V, VCE=600V, Rg=10Ω



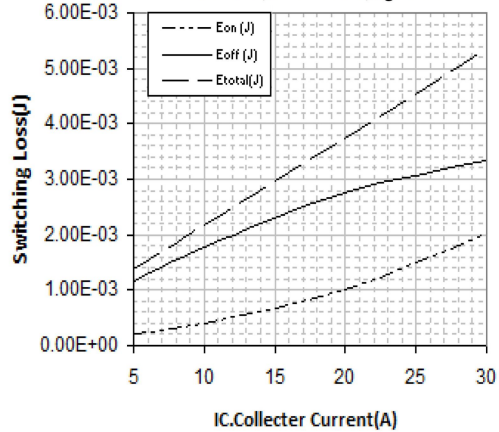
Switching Loss vs. IC(25°C)

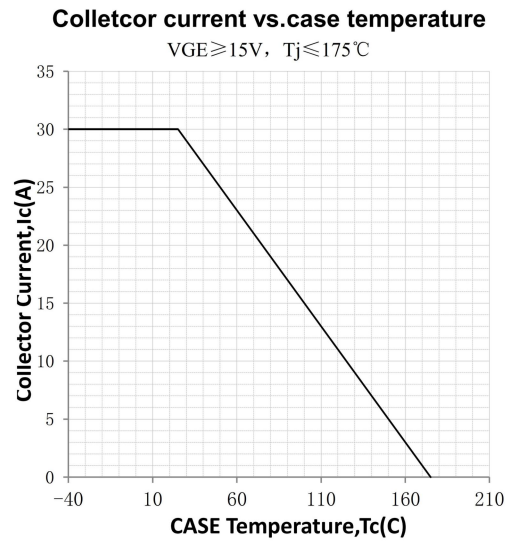
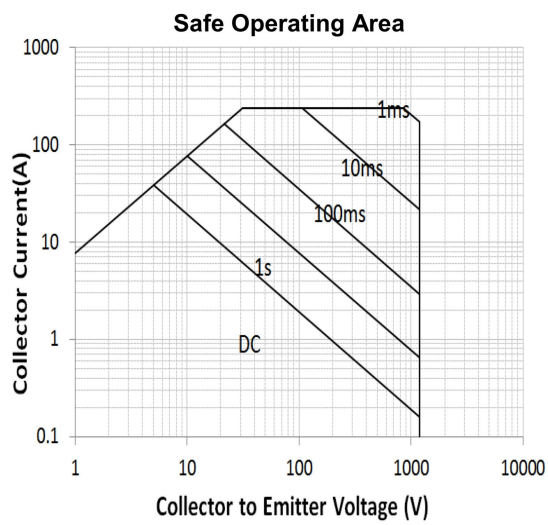
VGE=15V, VCE=600V, Rg=10Ω



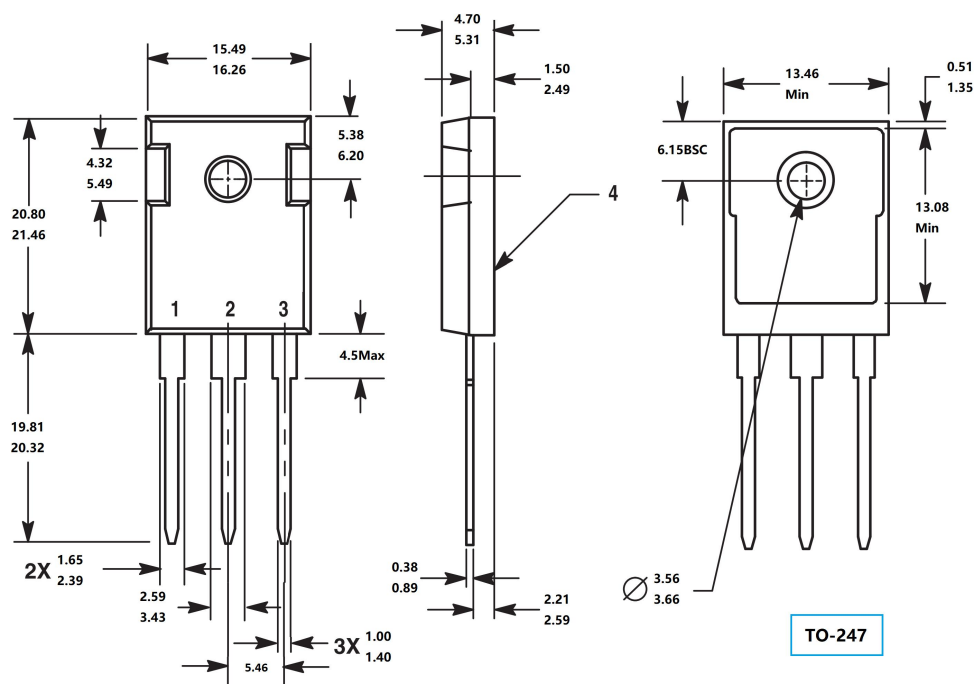
Switching Loss vs. IC(175°C)

VGE=15V, VCE=600V, Rg=10Ω





Package Mechanical DATA



X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [MASPOWER](#) manufacturer:

Other Similar products are found below :

[EST100BN120SN](#) [EST100BN60SN](#) [EST60BN120SN](#) [ESTF100SS60S](#) [ESTF15SS120C](#) [ESTF15SS135UC](#) [ESTF15SS60SC](#) [ESTF25D20SB](#)
[ESTF30S120U](#) [ESTF30SS60SC](#) [ESTF45D60U](#) [ESTF60SS120US](#) [ESTF60SS60US](#) [ESTF75D60U](#) [ESTF80D22U](#) [ESTF8SS120C](#)
[ESTF8SS195UP](#) [MS100N20HGC0](#) [MS100N20IDC0](#) [MS10N100HGC0](#) [MS10N100HGT1](#) [MS10N120HGC0](#) [MS10N40HGT0](#) [MS10N60FT](#)
[MS120N10FT](#) [MS120N15FB](#) [MS120N15FE](#) [MS12N100FC](#) [MS12N100FS](#) [MS12N100FT](#) [MS12N120HGC0](#) [MS12N120HJC0](#)
[MS13N20HGD0](#) [MS140N30HGB3](#) [MS140N30HGC0](#) [MS15N100HGC0](#) [MS15N100HGT1](#) [MS15N120HGC0](#) [MS170N15IDC0](#)
[MS170N25HGF4](#) [MS170N65HGF4](#) [MS18N100HGC0](#) [MS18N20FT](#) [MS20N50FS](#) [MS30N100HGC0](#) [MS33N10FT](#) [MS33N20HGC0](#)
[MS38N65FCC](#) [MS3N06FF](#) [MS3N100HGD0](#)